



AMERICAN
MICROSEMICONDUCTOR

AP1052 Transistors

Si PNP Power BJT

Military/High-Rel N

V(BR)CEO (V) 200

V(BR)CBO (V) 220

I(C) Max. (A) 10

Absolute Max. Power Diss. (W)

Maximum Operating Temp (°C)

I(CBO) Max. (A)

@V(CBO) (V) (Test Condition)

V(CE)sat Max. (V)

@I(C) (A) (Test Condition)

@I(B) (A) (Test Condition)

h(FE) Min. Current gain. 15

h(FE) Max. Current gain. 120

@I(C) (A) (Test Condition) 5.0

@V(CE) (V) (Test Condition) 5.0

f(T) Min. (Hz) Transition Freq 60M

@I(C) (A) (Test Condition)

@V(CE) (V) (Test Condition)

t(d) Max. (s) Delay time.

t(r) Max. (s) Rise time